

ABSTRACT OF THE DISCLOSURE

A bit line pre-charge circuit of a semiconductor memory device includes a pre-charge circuit connected between a pair of bit lines for pre-charging the pair of bit lines in response to a pre-charge control signal and a pre-charge voltage transmitting circuit for transmitting a pre-charge voltage to the pre-charge circuit in response to the pre-charge control signal. A voltage drop in a pre-charge voltage generation line may be prevented when a short circuit is formed between a word line and a pair of bit lines, and current consumption during a standby operation of the semiconductor memory device may also be reduced, by preventing current from flowing from the pair of bit lines to the pre-charge voltage generation line.